

عنوان مقاله:

Investigation of the As, Ga, B and N-doped (6,0) aluminumphosphide nanotubes interactions with H₂S gas: DFT study

محل انتشار:

سومین کنفرانس بین المللی دستاوردهای نوین پژوهشی در شیمی و مهندسی شیمی (سال: 1395)

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نویسندگان:

Maryam Zaboli - *Department of chemistry, University of Birjand, Birjand, Iran*

Heidar Raissi - *Department of chemistry, University of Birjand, Birjand, Iran*

Farzaneh Farzad - *Department of chemistry, University of Birjand, Birjand, Iran*

خلاصه مقاله:

The adsorption behavior of H₂S gas molecule on the surface of As, Ga, B and N-doped aluminum phosphide nanotubes are investigated by performing density functional theory calculations. The chemical potential for gas molecule and all studied complexes have been systematically explored. The AIM theory has been also used to examine the properties of the bond critical points: their electron densities and Laplacians. The As-doped nanotube with the adsorption energy of -9.82 kJ/mol has more tendency to the adsorption of H₂S gas than the other doped nanotubes. According to the obtained results, the process of H₂S molecule adsorption on the surface of As and N-doped AIPNT are exothermic

کلمات کلیدی:

doped-AIPNT, gas adsorption, density functional theory, AIM, HOMO and LUMO

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